Doc No. TT4-EA-13185

Revision. 3

MOS FET

FK3503010L

Panasonic

FK3503010L

Silicon N-channel MOSFET

For switching FK330301 in SMini3 type package

Features

Low drive voltage: 2.5 V drive
Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)

■ Marking Symbol: X1

Established: 2011-05-13

Revised

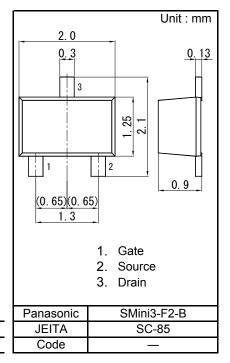
: 2013-08-28

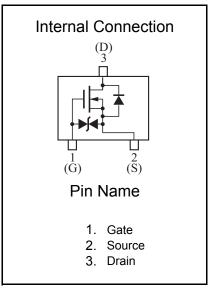
■ Packaging

Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)

■ Absolute Maximum Ratings Ta = 25 °C

Parameter	Symbol	Rating	Unit
Drain-source voltage	VDS	30	V
Gate-source voltage	VGS	±12	V
Drain current	ID	100	mA
Pulse drain current	IDp	200	mA
Total power dissipation	PD	150	mW
Channel temperature	Tch	150	°C
Operating ambient temperature	Topr	-40 to + 85	°C
Storage temperature	Tstg	-55 to +150	°C





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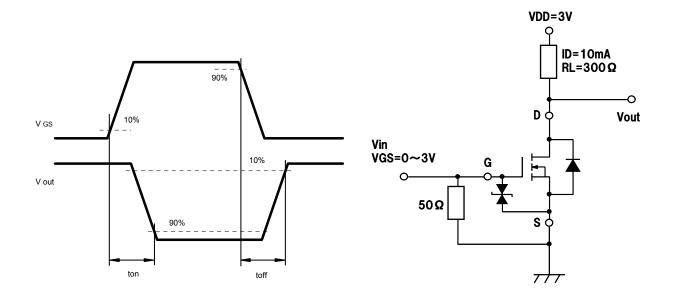
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■ Electrical Characteristics Ta = 25 °C ± 3 °C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-source breakdown voltage	VDSS	ID = 1 mA, VGS = 0	30			V
Drain-source cutoff current	IDSS	VDS = 30 V, VGS = 0			1.0	μΑ
Gate-source cutoff current	IGSS	VGS = ±10 V, VDS = 0			±10	μΑ
Gate threshold voltage	VTH	ID = 1.0 μA, VDS = 3.0 V	0.5	1.0	1.5	V
Drain-source ON resistance	RDS(on)	ID = 10 mA, VGS = 2.5 V		3	6	Ω
		ID = 10 mA, VGS = 4.0 V		2	3	Ω
Forward transfer admittance	Yfs	ID = 10 mA, VDS = 3.0 V	20	55		mS
Input capacitance	Ciss			12		pF
Output capacitance	Coss	VDS = 3 V, VGS = 0, f = 1 MHz		7		pF
Reverse transfer capacitance	Crss			3		pF
Turn-on time *1	ton	VDD = 3 V, VGS = 0 to 3 V		100		ns
		ID = 10 mA				
Turn-off time *1	toff	VDD = 3 V, VGS = 3 to 0 V		100		no
		ID = 10 mA		100		ns

1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

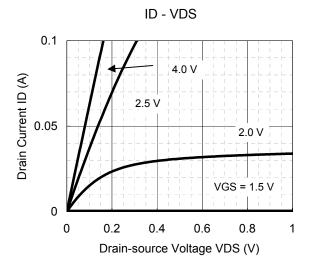
2. *1 Turn-on and Turn-off test circuit

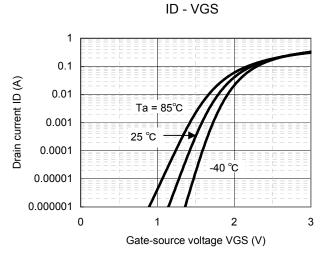


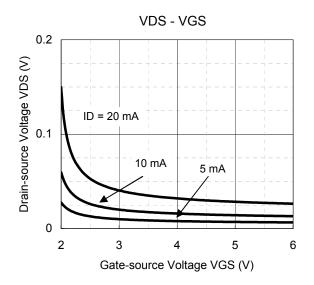
Established: 2011-05-13 Revised

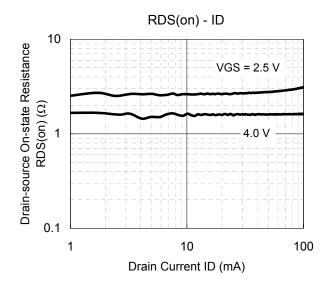
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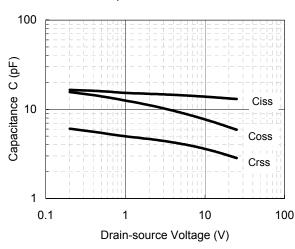








Capacitance - VDS



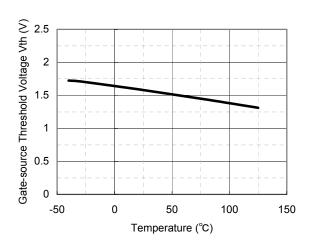
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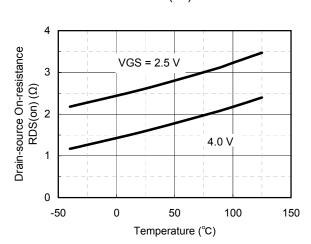
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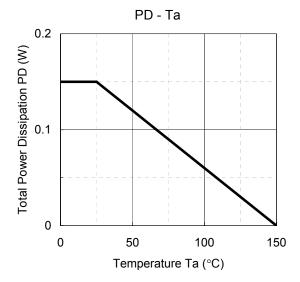


Vth - Ta

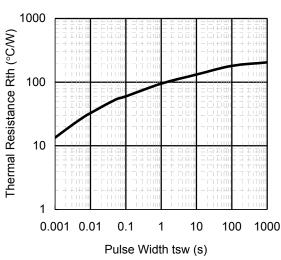


RDS(on) - Ta

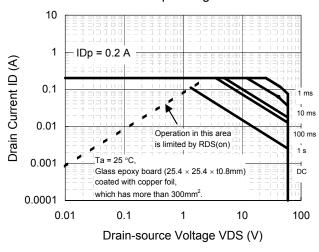




Rth -tsw



Safe Operating Area



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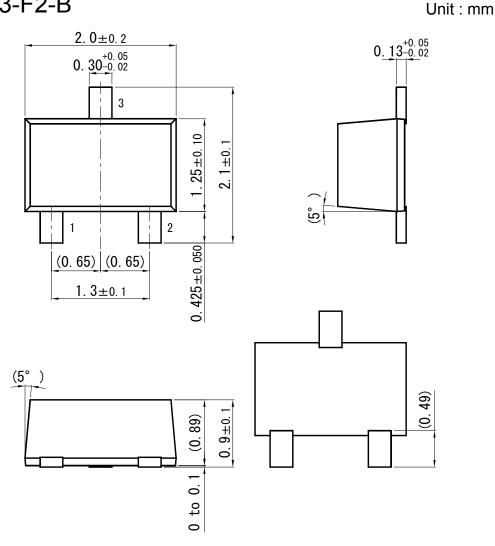
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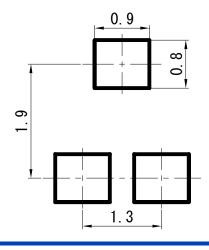
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SMini3-F2-B



■ Land Pattern (Reference) (Unit: mm)



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